

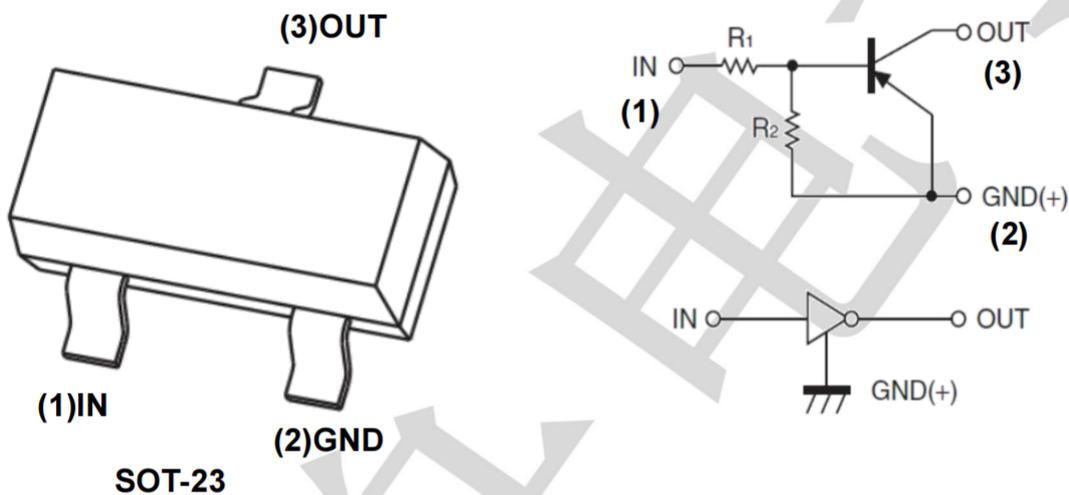
Product Summary

- VCC = -50V
- IC = -100mA
- R1 = 47kΩ
- R2 = 22kΩ

Features

- Built-in bias resistors
- making device design easy
- almost completely eliminating parasitic effects

Circuit diagram and pin information



Absolute Maximum Ratings

($T_A=25^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	LIMIT	UNIT
Supply Voltage	VCC	-50	V
Input Voltage	VIN	-40~+10V	V
Collector current	IC	-100	mA
Power Total Dissipation @ $T_A=25^{\circ}\text{C}$	P_D	200	mW
Maximum Operating Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature Range	TSTG	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics

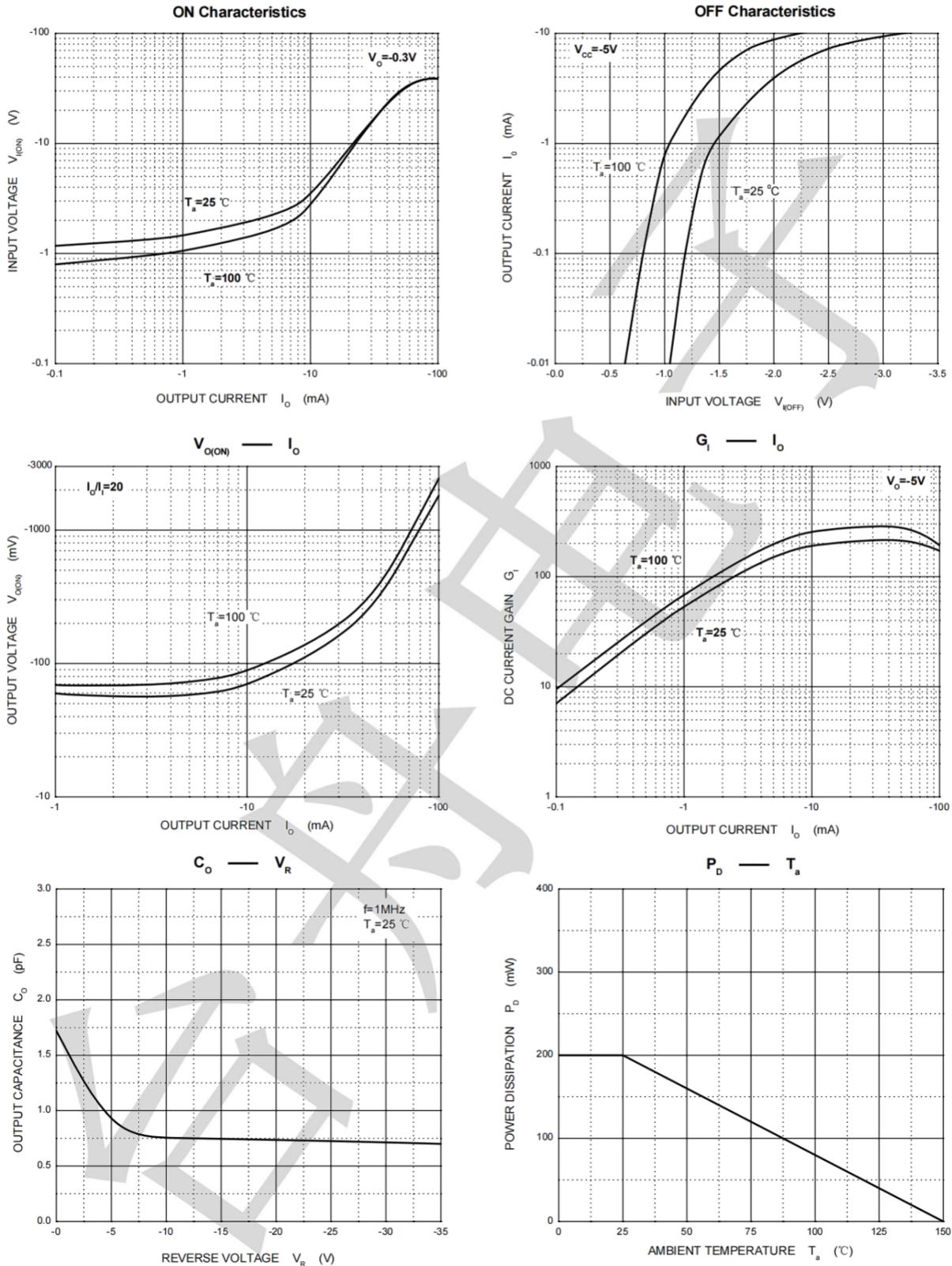
(TA=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input voltage	$V_{I(off)}$	$V_{CC}=-5V, I_O=-100\mu A$	-0.5	--	--	V
	$V_{I(on)}$	$V_O=-0.3V, I_O=-2mA$	--	--	-3	V
Output voltage	$V_{O(on)}$	$I_O/I_I=-10mA/-0.5mA$	--	--	-0.3	V
Input current	I_I	$V_I=-5V$	--	--	-1.8	mA
Output current	$I_{O(off)}$	$V_{CC}=-50V, V_I=0$	--	--	-0.5	μA
DC current gain	G_I	$V_O=-5V, I_O=-10mA$	60	--	--	--
Input resistance	R_1		32.9	47	61.1	k Ω
Resistance ratio	R_2/R_1		0.37	0.47	0.57	--
Transition frequency	f_T	$V_O=-10V, I_O=-5mA,$ $=100MHz$	--	250	--	MHz

Note:

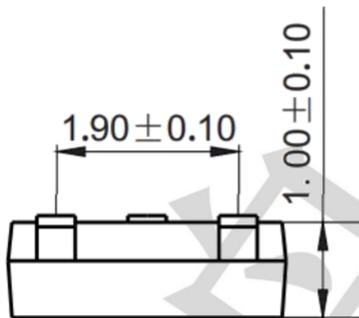
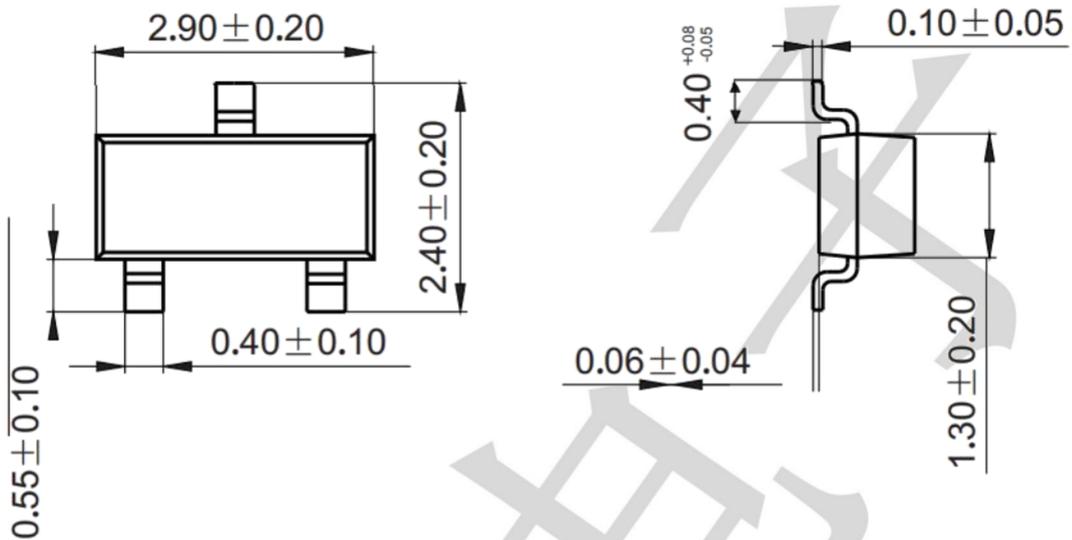
- 1.Characteristics of built-in transistor
- 2.Each terminal mounted on a reference land

Typical Performance Characteristics(TA=25°C)



Package Outline Dimensions (unit: mm)

SOT-23



Mounting Pad Layout (unit: mm)

